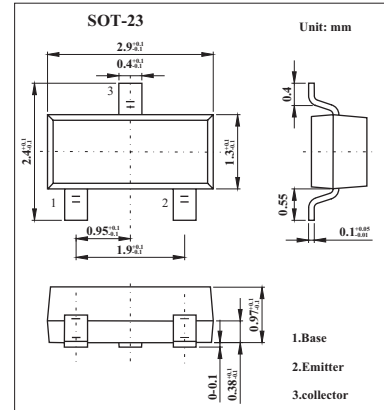


■ Features

- Excellent hFE linearity
- Collector Current :Ic=-0.5A



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-40	V
Collector - Emitter Voltage	V _{CE0}	-25	V
Emitter - Base Voltage	V _{EB0}	-5	V
Collector Current to Continuous	I _C	-500	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector - base breakdown voltage	V _{CB0}	I _C = -100μA, I _E = 0	-40			V
Collector - emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B = 0	-25			V
Emitter - base breakdown voltage	V _{EB0}	I _E = -100μA, I _C = 0	-5			V
Collector cut - off current	I _{CB0}	V _{CB} = -40V, I _E = 0			-0.1	μA
Collector cut - off current	I _{CE0}	V _{CB} = -20V, I _E = 0			-0.1	μA
Emitter cut - off current	I _{EB0}	V _{EB} = -5V, I _C = 0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -1V, I _C = -50mA	120		400	
Collector - emitter saturation voltage	V _{CE(sat)}	I _C = -500 mA, I _B = -50mA			-0.6	V
Base - emitter voltage	V _{BE(sat)}	I _C = -500 mA, I _B = -50mA			-1.2	V
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz			5	pF
Transition frequency	f _T	V _{CE} = -6V, I _C = -20mA, f = 30MHz	150			MHz

■ hFE Classification

Marking	2T1		
Rank	L	H	J
hFE	120~200	200~350	300~400

■ Typical Characteristics

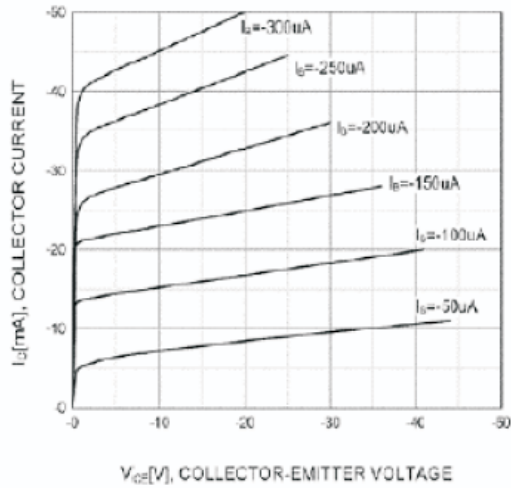


Fig.1 Static Characteristic

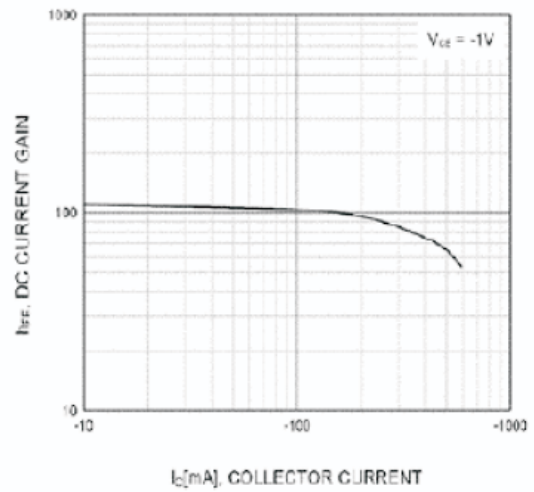


Fig.2 DC Current Gain

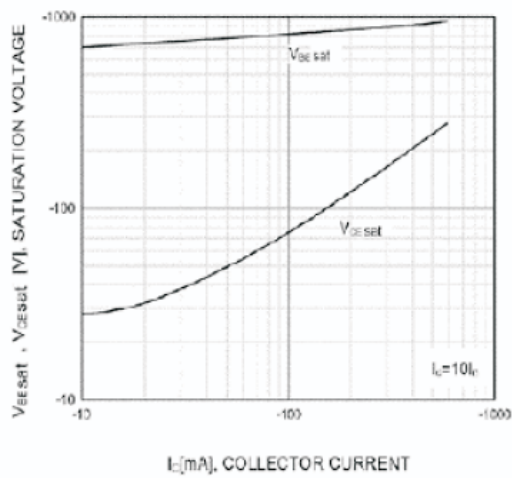


Fig.3 Base-Emitter Saturation Voltage
Collector- Emitter Saturation Voltage

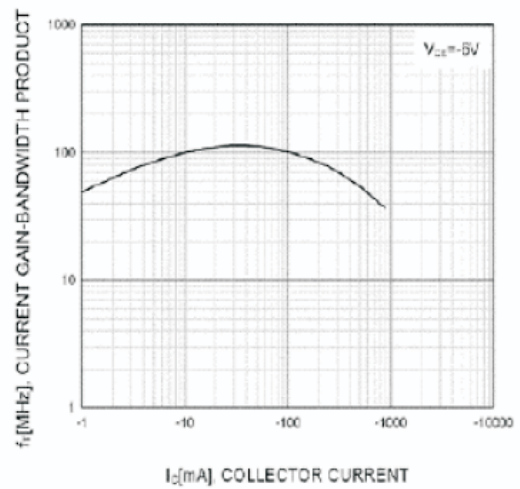


Fig.4 Current Gain Bandwidth Product